PNP/NPN Epitaxial Planar Silicon Transistors



2SA1704/2SC4484

High-Current Driver Applications

Applications

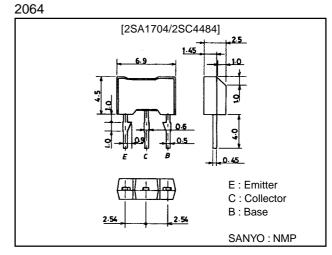
· Voltage regulators, relay drivers. lamp drivers.

Features

- · Adoption of FBET, MBIT processes.
- · Low collector-to-emitter voltage.
- · Large current capacity and wide ASO.
- · Fast switching speed.

Package Dimensions

unit:mm



():2SA1704

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(–)30	V
Collector-to-Emitter Voltage	VCEO		(–)25	V
Emitter-to-Base Voltage	VEBO		(–)6	V
Collector Current	IC		(–)2.5	А
Collector Current (Pulse)	ICP		(–)5	А
Collector Dissipation	PC		1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
Falanielei			min	typ	max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)50V, I _E =0			(–)100	nA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)100	nA
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)100mA	100*		400*	
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)1A	65			
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)50mA		150		MHz

 \ast : The 2SA1704/2SC4484 are classified by 100mA h_{FE} as follows :



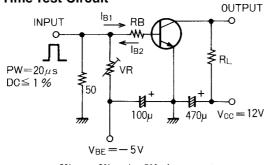
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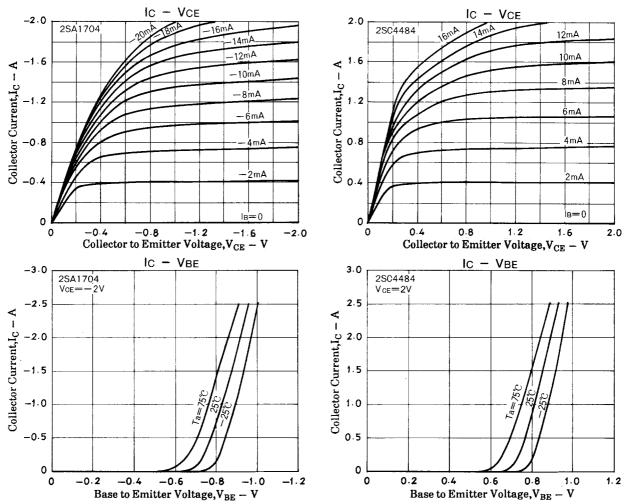
	Parameter	Symbol	Que ditions	Ratings			Unit
Collector-to-Emitter Saturation Voltage Base-to-Emitter Saturation Voltage Output Capacitance WWW.da Collector-to-Emitter Breakdown Voltage Collector-to-Emitter Breakdown Voltage Emitter-to-Base Breakdown Votage Turn-ON TIme Storage Time Fall Time	Symbol	Conditions	min	typ	max	Unit	
	Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =(-)1.5A, I _B =(-)75mA		(-0.35)	(-0.6)	V
					0.18	0.4	V
	Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)1.5A, I _B =(-)75mA		(–)0.95	(–)1.2	V
	Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(32)19		pF
	Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10μA, I _E =0	(–)30			V
	Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(–)1mA, R _{BE} =∞	(–)25			V
	Emitter-to-Base Breakdown Votage	V(BR)EBO	I _E =(-)10μA, I _C =0	(–)6			V
	Turn-ON TIme	ton	See specified Test Circuit		60		ns
	Storage Time	tstg	See specified Test Circuit		(350)		ns
		-			500		ns
	Fall Time	t _f	See specified Test Circuit		25		ns

Switching Time Test Circuit

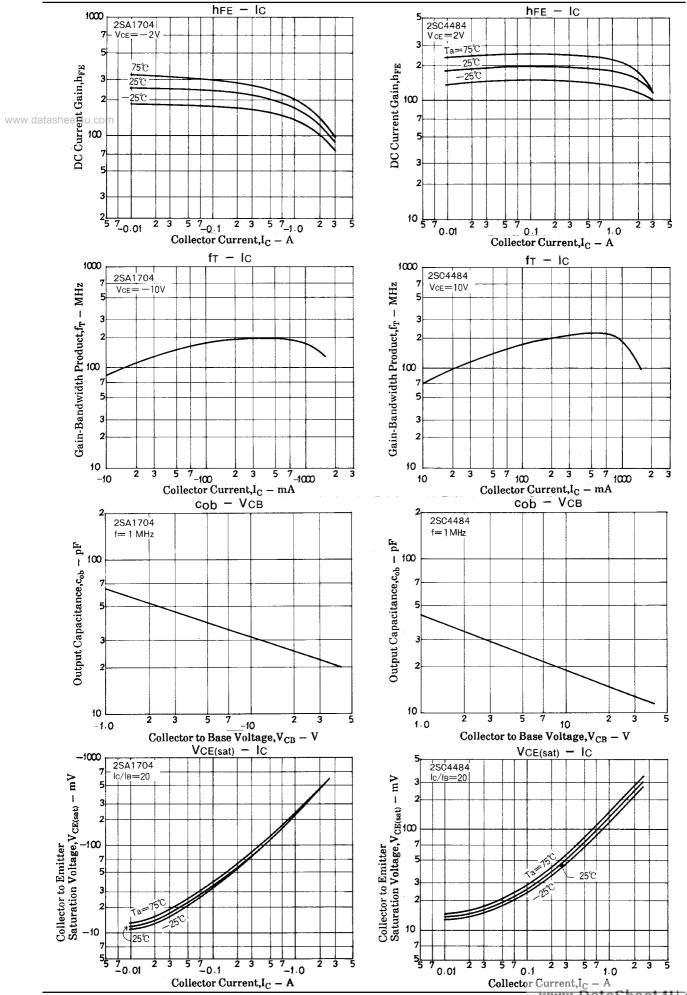


201B1=-201B2=1c=500mA

(For PNP, the polarity is reversed.) Unit (resistance : Ω , capacitance : F)



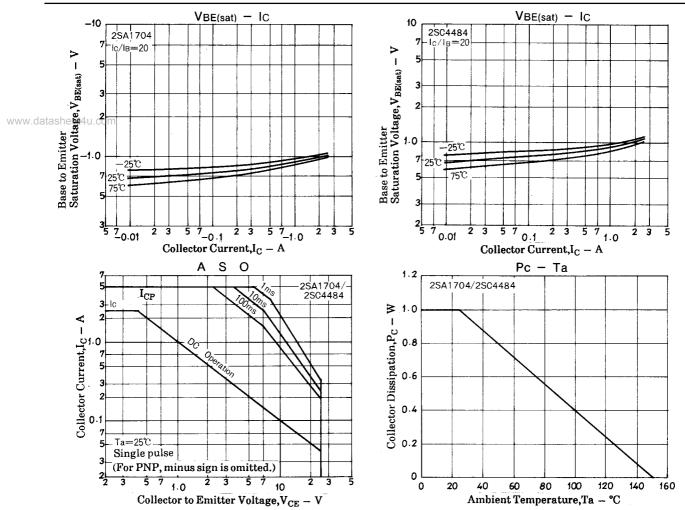
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